

S8550 S8550A M8550 MMT8550 SS8550 A6801

SOT—23 1. BASE 2. EMITTER 3. COLLECTOR



### ■FEATURES 特點

Low Frequency Power Amplifier 低頻功率放大 Suitable for Driver Stage If Small Motor 小馬達驅動 Complementary to 8050 与8050

## ■最大額定值(Ta=25℃)

CHARACTERISTIC 特性參數	Symbol 符號	Rating 額定値	Unit 單位
Collector-Base Voltage 集電極-基極電壓	$V_{CBO}$	-40 -25(A6801)	Vdc
Collect-Emitter Voltage 集電極-發射極電壓	V <sub>CEO</sub>	-25 -18(A6801)	Vdc
Emitter-Base Voltage 發射極-基極電壓	$\mathrm{V}_{\mathrm{EBO}}$	-5.0	Vdc
Collector Current 集電極電流	Ic	-500(88550A,88550) -1000(M8550) -1200(MMT8550) -1500(888550) -1800(A6801)	mAdc
Collector Power Dissipation 集電極耗散功率	P <sub>C</sub>	225	mW
Junction Temperature 結溫	T <sub>j</sub>	150	°C
Storage Temperature Range 儲存溫度	T <sub>stg</sub>	-55~150	°C

## ■DEVICE MARKING 打標

S8550	A=2TY.	S8550=2TY	M8550=Y2.	
MMT	°8550=Y2	SS8550=Y.2	A6801=6801	
■H <sub>FE</sub>	RANGE	女大倍數分檔		
H <sub>FE</sub>	(85~150	), (120~220)		
	(200~300	), (280~400)		

KEL 8550



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# ■ELECTRICAL CHARACTERISTICS 電特性

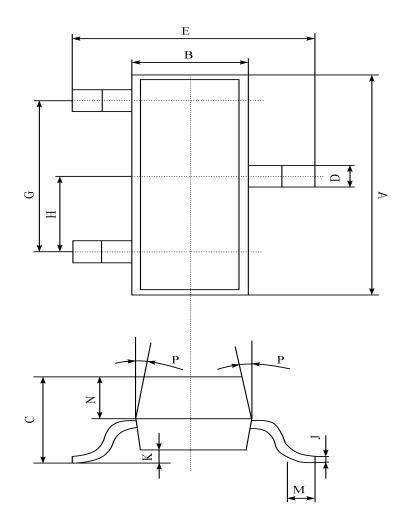
(T<sub>A</sub>=25℃ unless otherwise noted 如無特殊說明,溫度爲 25℃)

	1			1		
Characterstic 特性參數	Symbol 符號	Test Condition 測試條件	Min. 最小値	Typ. 典型值	Max. 最大値	Unit 單位
Collector Cutoff Current 集電極截止電流	I <sub>CBO</sub>	$V_{CB}$ =-30V, $I_{E}$ =0			-0.1	μA
Emitter Cutoff Current 發射極截止電流	I <sub>EBO</sub>	$V_{EB}$ =-5V,I <sub>C</sub> =0			-0.1	μA
Collector-Base Breakdown Voltage 集電極-基極擊穿電壓	V <sub>(BR)CBOO</sub>	I <sub>C</sub> =-100 μ A (A6801)	-40 (-25)			V
Collector-Emitter Breakdown Voltage 集電極-發射極擊穿電壓	V <sub>(BR)CEO</sub>	I <sub>C</sub> =-10mA (A6801)	-25 (-18)			V
Emitter-Base Breakdown Voltage 發射極-基極擊穿電壓	V <sub>(BR)EBO</sub>	$I_{E}$ =-100 $\mu$ A	-5			V
	$H_{FE}(1)$	V <sub>CE</sub> =-1V,I <sub>C</sub> =-100mA	85		400	
DC Current Gain 直流電流增益	H <sub>FE</sub> (2)	$V_{CE} = -1V,$ $I_{C} = -1800 \text{ mA}(\text{A6801})$ $I_{C} = -800 \text{ mA}$ (SS8550, MMT8550, M8550) $I_{C} = -500 \text{ mA}(\text{S8550})$ $I_{C} = -500 \text{ mA}(\text{S8550A})$	50 40 40 30			
Collector-Emitter Saturation Voltage 集電極-發射極飽和壓降	V <sub>CE(sat)</sub>	I <sub>C</sub> =-500mA, I <sub>B</sub> =-50mA			-0.6	V
Base-Emitter Voltage 基極-發射極電壓	$V_{BE}$	V <sub>CE</sub> =-1V,I <sub>C</sub> =-10mA		-0.8	-1.0	V
Transition Frequency 特徵頻率	f <sub>T</sub>	V <sub>CE</sub> =-5V,I <sub>C</sub> =-10mA	100	120		MHz
Collector Output Capacitance 輸出電容	C <sub>ob</sub>	V <sub>CB</sub> =-10V,I <sub>E</sub> =0,f=1MHz		13	30	pF



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### ■DIMENSION 外形封裝尺寸



序號	數值及公差	
Α	$2.90 \pm 0.10$	
В	$1.30 \pm 0.10$	
С	$1.00 \pm 0.10$	
D	$0.40 \pm 0.10$	
Е	$2.40 \pm 0.20$	
G	$1.90 \pm 0.10$	
Н	$0.95 \pm 0.05$	
J	$0.13 \pm 0.05$	
K	0.00-0.10	
М	≥0.2	
N	$0.60 \pm 0.10$	
Р	$7\pm2°$	

This datasheet presents technical data of Tak Cheong's Silicon Rectifier Diodes. Complete specifications for the individual devices are provided in the form of datasheets. A comprehensive Selector Guide is included to simplify the task of choosing the best set of components required for a specific application. For additional information, please visit our website <a href="http://www.takcheong.com">http://www.takcheong.com</a>.

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